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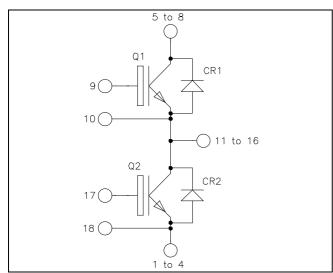


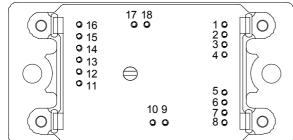






Phase leg Trench + Field Stop IGBT4 Power Module





Pins 1/2/3/4 ; 5/6/7/8 ; 11/12/13/14/15/16 must be shorted together

$V_{CES} = 1200V$ $I_C = 180A$ @ Tc = 80°C

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Trench + Field Stop IGBT 4 Technology
 - Low voltage drop
 - Low leakage current
 - Low switching losses
 - Soft recovery parallel diodes
 - Low diode VF
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive T_C of V_{CEsat}
- RoHS Compliant

All ratings @ $T_j = 25^{\circ}C$ unless otherwise specified

Absolute maximum ratings

Symbo	l Parameter		Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage		1200	V
I_{C}	Continuous Collector Current	$T_C = 25^{\circ}C$	220	
	Continuous Conector Current	$T_C = 80$ °C	180	A
I_{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	300	
V_{GE}	Gate – Emitter Voltage		±20	V
P_{D}	Maximum Power Dissipation	$T_C = 25^{\circ}C$	750	W
RBSO.	A Reverse Bias Safe Operating Area	$T_j = 125$ °C	300A @ 1100V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$				300	μΑ
V	Collector Emitter saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$		1.8	2.2	V
$V_{CE(sat)}$		$I_{\rm C} = 150 {\rm A}$ $T_{\rm j} = 150 {\rm °C}$		2.2		·	
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 5.5$ mA		5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				200	nA

Dynamic Characteristics

•	Characteristic	Test Conditions	Test Conditions		Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$			9.3		
C_{oes}	Output Capacitance	$V_{CE} = 25V$			0.58		nF
C_{res}	Reverse Transfer Capacitance	f = 1MHz	f = 1MHz		0.5		
Q_{G}	Gate charge	V_{GE} = -8V / 15V ; V_{CE} =600V I_{C} =150A			0.85		μС
$T_{d(on)}$	Turn-on Delay Time	Inductive Switch	hing (25°C)		130		
T_{r}	Rise Time	$V_{GE} = \pm 15V$			20		
$T_{d(off)}$	Turn-off Delay Time	$I_{\rm CE} = 600 \text{ V}$ $I_{\rm C} = 150 \text{ A}$	$V_{CE} = 600V$ $I_{CE} = 150 A$		300		ns
$T_{\rm f}$	Fall Time	$R_G = 3\Omega$			45		
$T_{d(on)}$	Turn-on Delay Time		Inductive Switching (150°C)		150		ns
T _r	Rise Time	$V_{GE} = \pm 15V$ $V_{CE} = 600V$ $I_{C} = 150A$ $R_{G} = 3\Omega$			35		
$T_{d(off)}$	Turn-off Delay Time				350		
$T_{\rm f}$	Fall Time				80		
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$ $V_{CE} = 600V$	$T_{\rm J} = 150^{\circ}{\rm C}$		13.5		mJ
E_{off}	Turn-off Switching Energy	$I_{\rm C} = 150 A$ $R_{\rm G} = 3 \Omega$	$T_J = 150$ °C		14.5		mJ
I_{sc}	Short Circuit data	$V_{GE} \le 15V ; V_{Bus} = 900V$ $t_p \le 10 \mu s ; T_j = 150 ^{\circ} C$			600		A
R_{thJC}	Junction to Case Thermal Resistance					0.20	°C/W

Reverse diode ratings and characteristics

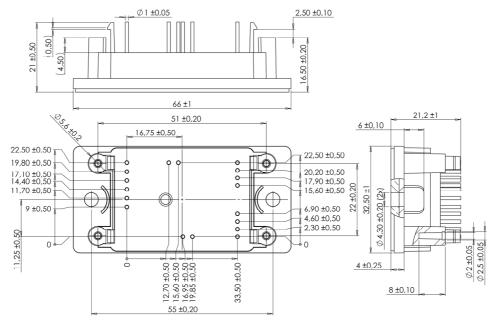
Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			1200			V
I_{RM}	Maximum Reverse Leakage Current	$V_R = 1200V$				100	μΑ
I_F	DC Forward Current		$Tc = 80^{\circ}C$		150		A
$V_{\rm F}$	Diode Forward Voltage	$I_F = 150A$ $T_j = 25^{\circ}$			1.7	2.2	V
V F		$V_{GE} = 0V$	$T_{i} = 150^{\circ}C$		1.65		· v
t _{rr}	Reverse Recovery Time		$T_j = 25$ °C		155		ns
ν _{rr}		1.704	$T_{j} = 150^{\circ}C$		300		113
0	Reverse Recovery Charge	$V_R = 600 V$ $di/dt = 3400 A/\mu s$	$T_j = 25$ °C		13.3		μС
Q_{rr}			$T_{j} = 150^{\circ}C$		27.6		
E _{rr}	Reverse Recovery Energy		$T_j = 25^{\circ}C$		5.9		mJ
			$T_{\rm j} = 150^{\circ}{\rm C}$		11.5		1113
R_{thJC}	Junction to Case Thermal Resistance		•			0.38	°C/W



Thermal and package characteristics

Symbol	Characteristic		Min	Тур	Max	Unit	
V_{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz			4000			V
T_{J}	Operating junction temperature range			-40		175	
T_{STG}	Storage Temperature Range			-40		125	°C
T_{C}	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M4	2		3	N.m
Wt	Package Weight					75	g

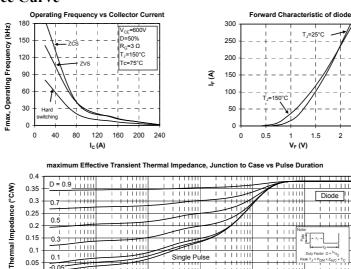
SP2 Package outline (dimensions in mm)



Typical Performance Curve

0.00001

0.0001



3 - 5

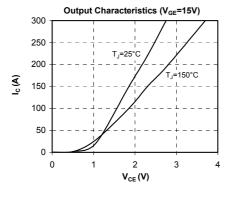
2 2.5

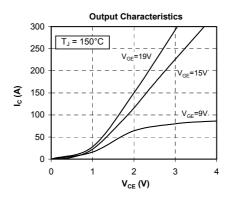
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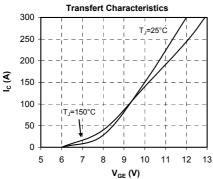
Rectangular Pulse Duration in Seconds

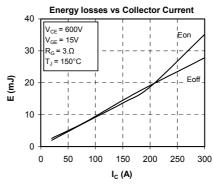
0.1

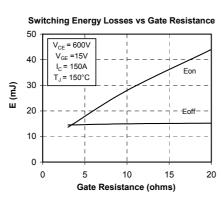


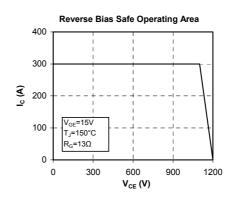


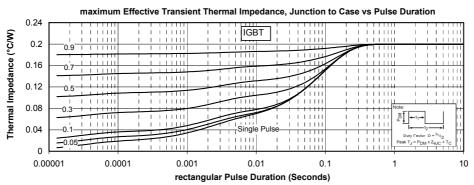












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